

Docket No. 243397US2TTCRD

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Tatsuo SHIMIZU, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: INSULATING FILM AND ELECTRONIC DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

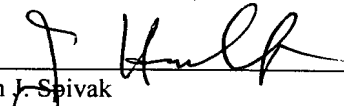
- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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STATEMENT OF RELEVANCY

Reference AO (2000-195856) of Form PTO-1449:

Structure is similar. But in this patent, energy levels are not quantized. This patent does not include ideas of quantum well structures.

Reference AP (2001-274393) of Form PTO-1449:

Structure is similar. But in this patent, energy levels are not quantized. This patent does not include ideas of quantum well structures.

Reference AQ (2002-100767) of Form PTO-1449:

This patent is about perovskite type gate oxides

Reference AW of Form PTO-1449:

This paper is about Ruddlesden-popper type oxides. This paper does not include ideas of quantum well structure. In our patent, quantum well structure can make the barrier height of a gate oxide as high as that of a barrier material.

Reference AX of Form PTO-1449:

This paper is about perovskite type oxides. This paper includes rocksalt and perovskite double-layers structures, but does not include quantum well structures.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

243397US2TTCRD

SERIAL NO.

New Application

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Tatsuo SHIMIZU, et al.

FILING DATE

Herewith

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	2000-195856	07/14/00	Japan		X
	AP	2001-274393	10/05/01	Japan		X
	AQ	2002-100767	04/05/02	Japan		X
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	J. H. HAENI, et al., "EPITAXIAL GROWTH OF THE FIRST FIVE MEMBERS OF THE $\text{Sr}_{n+1}\text{Ti}_n\text{O}_{3n+1}$ RUDDLESDEN-POPPER HOMOLOGOUS SERIES" Applied Physics Letters, Volume 78, Number 21, May 21, 2001, pgs. 3292 – 3294.
	AX	R. A. McKEE, et al., "PHYSICAL STRUCTURE AND INVERSION CHARGE AT A SEMICONDUCTOR INTERFACE WITH A CRYSTALLINE OXIDE", Science, Vol. 293, July 20, 2001, pgs. 468 – 471.
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.